

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S35	471	((silicon with germanium) SiGe) and (anneal\$5 with diffus\$5) and (chemical\$1mechanical cmp)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 21:08
S57	1	"20040214407"	US-PGPUB; USPAT	OR	ON	2006/04/28 13:57
S58	8	(438/796.ccls: 438/797.ccls:) and @pd>"20051019"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 12:47
S59	1	"20040031979"	US-PGPUB; USPAT	OR	ON	2006/04/28 15:35
S60	511	((chemical adj mechanical adj polish\$5) CMP) and (mirror adj finish\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 15:57
S61	12	S60 and (root adj mean adj square)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 15:36
S62	1337	((chemical adj mechanical adj polish\$5) CMP) and ((root adj mean adj square) rms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:00
S63	1059	((root adj mean adj square) rms) same angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:02
S64	135	S62 and S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:01
S65	50	((root adj mean adj square) rms) same (angstrom near "1")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:02

*Alm*

## EAST Search History

S66	50	S63 and S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:29
S67	2961	(haze roughness) with wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:30
S68	544	S67 and (haze with wavelength)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
S69	144097	(layer near semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
S70	20	S68 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
S71	4	(horizontal near flow) with (deposition near (apparatus reactor chamber))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 20:12
S72	1	1988-292796.NRAN.	DERWENT	OR	ON	2006/04/28 20:10
S73	64	((horizontal near flow) and ((chemical adj vapor adj deposition) CVD) and ((rotate rotated rotating spin\$5) near (substrate wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 20:46
S74	6	((rotate rotated rotating spin\$5) near (substrate wafer)) and (((leading near edge) near (substrate wafer)) with (concentration fraction composition))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 20:47